Application No.: 10/613,331 Docket No.: 29926/39487

## AMENDMENTS TO THE SPECIFICATION

Please amend page 7, line 20 to page 8, line 6 as follows:

During a <u>an</u> insulation layer 26 etch process, fluorine (F) containing plasma gas such as C<sub>2</sub>F<sub>4</sub>, C<sub>2</sub>F<sub>6</sub>, C<sub>3</sub>F<sub>8</sub>, C<sub>4</sub>F<sub>6</sub>, C<sub>5</sub>F<sub>8</sub> or C<sub>6</sub>F<sub>6</sub>, i.e., C<sub>x</sub>F<sub>y</sub>, wherein x and y ranges from 1 to 10 is generally used as a main etching gas during the SAC process. Herein, such gas for generating a polymer during the SAC process, i.e., CH<sub>2</sub>F<sub>2</sub>, C<sub>3</sub>HF<sub>5</sub> or CHF<sub>3</sub> is also added thereto. At this time, an inert gas such as helium (He), neon (Ne), argon (Ar) or xenon (Xe) is used as a carrier gas. Accordingly, it is possible to obtain an etching profile of the SAC process capable of minimizing damage of a gate hard mask 23 by protecting an upper area of the gate hard mask 23. Next, the photo-resist pattern and etching remnants are removed by performing a photo-resist strip process and a cleaning process, respectively.